

## ABSTRACT OF THE DISCLOSURE

A lateral-current-flow integrated transistor, formed in an epitaxial layer defining a base well with a first conductivity type, which accommodates emitter and collector regions of a second conductivity type. The collector region is formed by an internal conductive region and by an external conductive region, and the emitter region is formed by an intermediate conductive region. The external conductive region has an annular shape and surrounds the intermediate conductive region, which also has an annular shape and surrounds the internal conductive region.

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